INTEGRATED CIRCUITS

DATA SHEET

NE/SA/AU5232

Matched dual high-performance low-voltage operational amplifier

Product data 2002 May 21





Matched dual high-performance low-voltage operational amplifier

NE/SA/AU5232

DESCRIPTION

The NE/SA/AU5232 is a matched, low voltage, high performance dual operational amplifier. Among its unique input and output characteristics is the capability for both input and output rail-to-rail operation, particularly critical in low voltage applications. The output swings to less than 50 mV of both rails across the entire power supply range. The NE/SA/AU5232 is capable of delivering 5.5 V peak-to-peak across a 600 Ω load and will typically draw only 700 μ A per amplifier. The bandwidth is 2.5 MHz and the 1% settling time is 1.4 μ s.

FEATURES

- Wide common-mode input voltage range: 250 mV beyond both rails
- Output swing within 50 mV of both rails
- Functionality to 1.8 V typical
- Low current consumption: 700 μA per amplifier
- ±15 mA output current capability
- Unity gain bandwidth: 2.5 MHz
- Slew rate: 0.8 V/μs
- Low noise: 33 nV/√Hz
- Electrostatic discharge protection
- Short-circuit protection
- Output inversion prevention

PIN CONFIGURATION

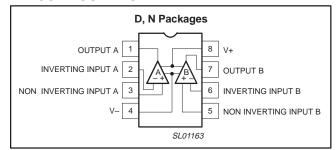


Figure 1. Pin configuration.

APPLICATIONS

- Automotive electronics
- Signal conditioning and sensing amplification
- Portable instrumentation
 - Test and measurement
 - Medical monitors and diagnostics
 - Remote meters
- Audio equipment
- Security systems
- Communications
 - Pagers
 - Cellular telephone
 - LAN
- 5 V Datacom bus
- Error amplifier in motor drives
- Transducer buffer amplifier

ORDERING INFORMATION

ORDER CODE	DESCRIPTION	TEMPERATURE RANGE	DWG #
NE5232D	8-Pin Plastic Small Outline (SO) package	0 °C to +70 °C	SOT96-1
NE5232N	8-Pin Plastic Dual In-Line Package (DIP)	0 °C to +70 °C	SOT97-1
SA5232D	8-Pin Plastic Small Outline (SO) package	–40 °C to +85 °C	SOT96-1
SA5232N	8-Pin Plastic Dual In-Line Package (DIP)	–40 °C to +85 °C	SOT97-1
AU5232N	8-Pin Plastic Dual In-Line Package (DIP)	−40 °C to +125 °C	SOT97-1
AU5232D	8-Pin Plastic Small Outline (SO) package	-40 °C to +125 °C	SOT96-1

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ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Single supply voltage	7	V
V _{ESD}	ESD protection voltage at any pin ⁵ human body model robot model	2000 200	V
Vs	Dual supply voltage	±3.5	V
V_{DP}	Voltage at any device pin ¹	V _S ± 0.5	V
I _{DP}	Current into any device pin ¹	±50	mA
V _{i(dif)}	Differential input voltage ²	0.5	V
V _{i(CM)}	Common-mode input voltage (positive)	V _{CC} + 0.5	V
V _{i(CM)}	Common-mode input voltage (negative)	V _{EE} - 0.5	V
P _D	Power dissipation ³	500	mW
T _j	Operating junction temperature ³	+150	°C
V _{SC}	Supply voltage allowing indefinite output short circuit to either rail ^{3,4}	7	V
T _{stg}	Storage temperature range	-65 to +150	°C
T _{sld}	Lead soldering temperature (10 sec max)	+230	°C
$\theta_{\sf JA}$	Thermal impedance 8-pin plastic DIP 8-pin plastic SO		°C/W °C/W

NOTES:

- Each pin is protected by ESD diodes. The voltage at any pin is limited by the ESD diodes.
 The differential input of each amplifier is limited by two internal diodes, connected in parallel and opposite to each other. For more differential input range, use differential resistors in series with the input pins.
- The maximum operating junction temperature is +150 °C. At elevated temperatures, devices must be derated according to the package thermal resistance and device mounting conditions. Derates above +25 °C: N package at 9.5 mW/°C; D package at 6.25 mW/°C.
- Simultaneous short circuits of two amplifiers to the positive or negative rail can exceed the power dissipation ratings and cause eventual destruction of the device.
- 5. Guaranteed by design.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	RATING	UNIT			
V _{CC}	Single supply voltage	+2 to +5.5				
Vs	Dual supply voltage	±1 to ±2.75	V			
V _{i(CM)}	Common-mode input voltage (positive)	V _{CC} + 0.25	V			
V _{i(CM)}	Common-mode input voltage (negative)	V _{EE} – 0.25	V			
	Temperature					
т	NE	0 to +70	°C			
T_{amb}	SA	-40 to +85	°C			
	AU	-40 to +125	°C			

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DC ELECTRICAL CHARACTERISTICS

 V_{CC} = 2 V to 5.5 V, V_{EE} = 0 V, T_{amb} = 25 °C; V_{EE} < $V_{i(CM)}$ < V_{CC} ; unless otherwise stated.

		TEST CONDITIONS			LIM				
SYMBOL	PARAMETER	TEST CONDITIONS		NE5232	2		SA5232	2	UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
		$V_{CC} = 5.5V$		1.4	2.0		1.4	2.0	
I _{CC}	Supply current	V _{CC} = 5.5 V; over full temp. range		1.5	2.3		1.6	2.4	mA
\/	Offset voltage			±0.2	±4		±0.2	±4	mV
V _{OS}	Oliset voltage	Over full temp. range		±0.4	±5		±0.6	±5	''''
ΔV _{OS} /ΔT	Offset voltage drift with temperature			4			4		μV/°
ΔV _{OS}	Offset voltage difference between any amplifiers in			0.4	3		0.4	3	m _V
	the same package at the same common mode level ¹	Over full temp. range		0.8	4		1.2	4	
los	Offset current			±3	±20		±3	±30	l _{nA}
-00		Over full temp. range		±4	±30		±6	±60	
ΔI _{OS} /ΔT	Offset current drift with temperature			0.02	±.3		0.03	±.3	nA/°
		$V_{EE} < V_{i(CM)} < V_{EE} +0.5 V$	-200	-90		-200	-90		
I _B	Input bias current ¹	Over full temp. range	-225	-100		-250	-150		nA
'B	input bido odiront	V_{EE} +1 V < $V_{i(CM)}$ < V_{CC}		25	70		25	75	11/4
		Over full temp. range		35	100		35	120	
$\Delta I_{B}/\Delta T$	Input bias current drift with temperature			0.5			0.5		nA/°
	Input bias current	$V_{EE} < V_{i(CM)} < V_{EE} + 0.5 \text{ V}$		10	30		10	30	
Δl_{B}	difference between any amplifier in the same	Over full temp. range		25	50		50	70	nA
	package at the same	V_{EE} +1 V < $V_{i(CM)}$ < V_{CC}		5	20		5	20] ''′
	common mode level.	Over full temp. range		15	30		25	50	
		$V_{OS} \le 6 \text{ mV}$	V _{EE} -0.25		V _{CC} +0.25	V _{EE} -0.25		V _{CC} +0.25	
$V_{i(CM)}$	Common-mode input range	V _{OS} ≤ 6 mV; Over full temp. range	V _{EE} -0.1		V _{CC} +0.1	V _{EE} -0.1		V _{CC} +0.1	V
	Common-mode rejection ratio, small signal	$V_{EE} < V_{i(CM)} < V_{EE} + 0.5V;$ $V_{EE} + 1V < V_{i(CM)} < V_{CC}$	80	100		80	100		
CMRR	Tallo, Siliali Sigilal	Over full temp. range	75	100		75] dB
	Common-mode rejection	$V_{EE} < V_{i(CM)} < V_{CC}$	65	90		65	90		
	ratio, large signal	Over full temp. range	60	80		60			
PSRR	Power supply rejection	$V_{EE} < V_{i(CM)} < V_{CC}$	80	100		80	100		dB
FORK	ratio	Over full temp. range	80	90		80	90		
IL	Peak load current, sink and		10	12		10	12		m/
"L	source	Over full temp. range	5	8		5	8		1117
A_{VOL}	Open-loop voltage gain	Over full temp, range	90	110 90		90	110 90		dB
		I _{PEAK} = 0.1 mA	V _{EE} +0.05		V _{CC} -0.05	V _{EE} +0.1		V _{CC} -0.1	
	Output wells as audion	I _{PEAK} = 10 mA	V _{EE} +0.25		V _{CC} -0.25	V _{EE} +0.25		V _{CC} -0.25	1 .,
V _{OUT}	Output voltage swing	I _{PEAK} = 5 mA; over full temp. range	V _{EE} +0.22		V _{CC} -0.22	V _{EE} +0.2		V _{CC} -0.2	V
	Output voltage swing for	$R_L = 2 k\Omega$	V _{EE} +0.2		V _{CC} -0.2	V _{EE} +0.2		V _{CC} -0.2	
	$V_{CC} = 2.75 \text{ V}, V_{EE} = -2.75 \text{ V}$	R _I = 600 Ω	V _{EE} +0.25		V _{CC} -0.25	V _{EE} +0.25		V _{CC} -0.25	٧

NOTE:

These parameters are measured for V_{EE} < V_{CM} < V_{EE}+0.5 V and for V_{EE}+1 V < V_{CM} < V_{CC}. By design these parameters are intermediate for common mode ranges between the measured regions.

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DC ELECTRICAL CHARACTERISTICS

 V_{CC} = 2 V to 5.5 V, V_{EE} = 0 V, T_{amb} = 25 °C; V_{EE} < $V_{i(CM)}$ < V_{CC} ; unless otherwise stated.

SYMBOL	PARAMETER	TEST CONDITIONS		LIMITS AU5232		UNIT	
OTHEOL	TANAMETER		MIN	TYP	MAX	"""	
		V _{CC} = 5.5V		1.4	2.0		
I _{CC}	Supply current	$V_{CC} = 5.5 \text{ V};$ over full temp. range		1.6	2.4	mA	
.,	0"			±0.2	±4	.,	
V_{OS}	Offset voltage	Over full temp. range		±0.6	±5	mV	
ΔV _{OS} /ΔT	Offset voltage drift with temperature			4		μV/°C	
4)/	Offset voltage difference between any amplifiers in the			0.4	3	\/	
ΔV_{OS}	same package at the same common mode level ¹	Over full temp. range		1.2	4	mV	
	Office to compare to			±3	±30		
los	Offset current	Over full temp. range		±6	±60	nA	
Δl _{OS} /ΔT	Offset current drift with temperature			0.03	±.3	nA/°C	
		$V_{EE} < V_{i(CM)} < V_{EE} + 0.5 V$	-200	-90			
	January Indian arranged	Over full temp. range	-250	-150		1	
l _Β	Input bias current ¹	V _{EE} +1 V < V _{i(CM)} < V _{CC}		25	75	nA	
		Over full temp. range		35	120	1	
$\Delta I_B/\Delta T$	Input bias current drift with temperature			0.5		nA/°C	
		$V_{EE} < V_{i(CM)} < V_{EE} + 0.5 \text{ V}$		10	30		
Δl_{B}	Input bias current difference between any amplifier in the	Over full temp. range		50	70	1 .	
	same package at the same common mode level.	V _{EE} +1 V < V _{i(CM)} < V _{CC}		5	20	nA	
		Over full temp. range		25	50	1	
		V _{OS} ≤ 6 mV	V _{EE} -0.25		V _{CC} +0.25		
$V_{i(CM)}$	Common-mode input range	V _{OS} ≤ 6 mV; Over full temp. range	V _{EE} -0.1		V _{CC} +0.1	V	
	Common-mode rejection ratio, small signal	$V_{EE} < V_{i(CM)} < V_{EE} + 0.5V;$ $V_{EE} + 1V < V_{i(CM)} < V_{CC}$	80	100			
CMRR		Over full temp. range	70			dB	
	Common-mode rejection ratio, large signal	$V_{EE} < V_{i(CM)} < V_{CC}$	65	90			
	Common-mode rejection ratio, large signal	Over full temp. range	55				
PSRR	Power supply rejection ratio	$V_{EE} < V_{i(CM)} < V_{CC}$	80	100		dB	
FORK	Prower supply rejection ratio	Over full temp. range	75	90		U.B	
IL	Peak load current, sink and source		10	12		mA	
'L	T ear load current, sink and source	Over full temp. range	5	8			
Δ	Open-loop voltage gain		90	110		dB	
A _{VOL}	Open 100p voltage gain	Over full temp. range		90		ub	
		$I_{PEAK} = 0.1 \text{ mA}$	V _{EE} +0.1		V _{CC} -0.1		
	Output voltage swing	I _{PEAK} = 10 mA	V _{EE} +0.25		V _{CC} -0.25	V	
V_{OUT}		I _{PEAK} = 5 mA; over full temp. range	$I_{PEAK} = 5 \text{ mA};$ ver full temp. range $V_{EE} + 0.2$ $V_{CE} + 0.2$			1	
	Output voltage swing for	$R_L = 2 k\Omega$	V _{EE} +0.2		V _{CC} -0.2	V	
	$V_{CC} = 2.75 \text{ V}, V_{EE} = -2.75 \text{ V}$	$R_L = 600 \Omega$	V _{EE} +0.25		V _{CC} -0.25	1 °	

NOTE:

1. These parameters are measured for V_{EE} < V_{CM} < V_{EE}+0.5 V and for V_{EE}+1 V < V_{CM} < V_{CC}. By design these parameters are intermediate for common mode ranges between the measured regions.

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AC ELECTRICAL CHARACTERISTICS

 T_{amb} = +25 °C; V_{CC} = 2 V to 5.5 V; R_L = 10 k Ω ; C_L = 100 pF; unless otherwise stated.

					LIM	ITS			
SYMBOL	PARAMETER	TEST CONDITIONS		NE5232		S	A/AU523	2	UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate	Over full temperature range	0.5	0.8		0.5	0.8		V/μs
BW	Unity gain bandwidth: -3 dB	Over full temperature range	2	2.5	4.0	2	2.5	4.0	MHz
θ_{M}	Phase Margin	$C_L = 50 \text{ pF}$		55			55		deg
t _S	1% settling time	A _V = 1, 1 V step		1.4			1.4		μs
V _N	Input referred voltage noise	$A_V = 1$, $R_S = 0 \Omega$, at 1 kHz		33			33		nV/Hz ^{1/2}
THD	Total harmonic distortion	10 kHz, 1V _{P-P} , A _V = 1		0.1			0.1		%

OUTPUT INVERSION PREVENTION

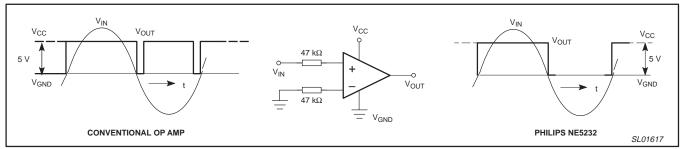
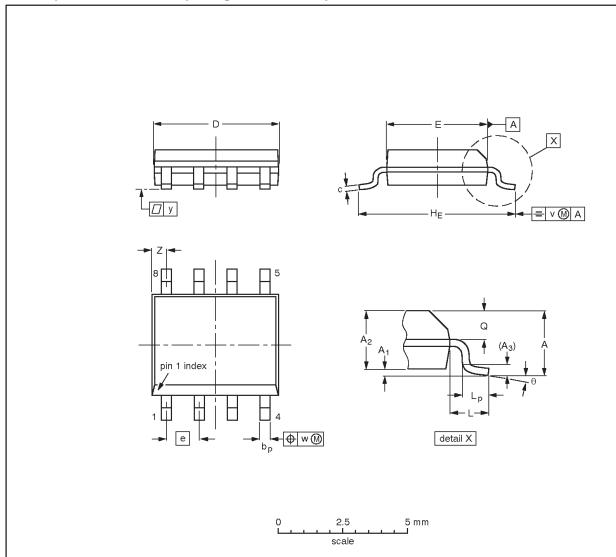


Figure 2. Output inversion prevention.

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	Α1	A ₂	A ₃	bр	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.20 0.19	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012			97-05-22 99-12-27

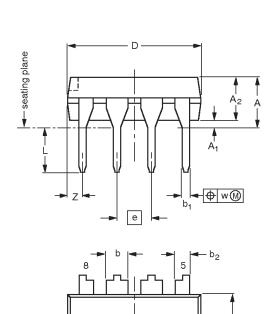
2002 May 21 7

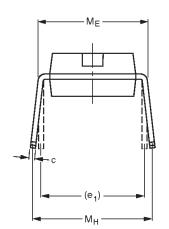
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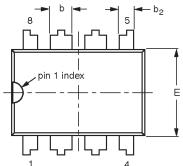
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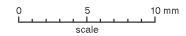
DIP8: plastic dual in-line package; 8 leads (300 mil)

SOT97-1









DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.14	0.53 0.38	1.07 0.89	0.36 0.23	9.8 9.2	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	1.15
inches	0.17	0.020	0.13	0.068 0.045	0.021 0.015	0.042 0.035	0.014 0.009	0.39 0.36	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.045

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ	PROJECTION	1330E DATE
SOT97-1	050G01	MO-001	SC-504-8		-95-02-04- 99-12-27

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NOTES

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Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definitions
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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^[1] Please consult the most recently issued data sheet before initiating or completing a design.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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